



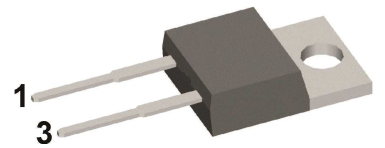
FRED

V_{RRM}	=	1200 V
I_{FAV}	=	12 A
t_{rr}	=	50 ns

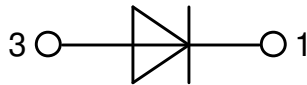
Fast Recovery Epitaxial Diode Single Diode

Part number

DSEI12-12A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1200	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current, drain current	$V_R = 1200\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		250	μA
		$V_R = 960\text{ V}$		$T_{VJ} = 125^\circ\text{C}$		4	mA
V_F	forward voltage drop	$I_F = 12\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		2,58	V
		$I_F = 24\text{ A}$				2,94	V
		$I_F = 12\text{ A}$		$T_{VJ} = 150^\circ\text{C}$		2,23	V
		$I_F = 24\text{ A}$				2,72	V
I_{FAV}	average forward current	$T_C = 100^\circ\text{C}$ rectangular	$d = 0.5$	$T_{VJ} = 150^\circ\text{C}$		12	A
V_{FO}	threshold voltage	} for power loss calculation only				1,77	V
r_F	slope resistance					38	m Ω
R_{thJC}	thermal resistance junction to case					1,6	K/W
R_{thCH}	thermal resistance case to heatsink					0,50	K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		78	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		75	A
C_J	junction capacitance	$V_R = 600\text{ V}$ $f = 1\text{ MHz}$		$T_{VJ} = 25^\circ\text{C}$		6	pF
I_{RM}	max. reverse recovery current	} $I_F = 11\text{ A}; V_R = 540\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		4	A
				$T_{VJ} = 100^\circ\text{C}$		6	A
t_{rr}	reverse recovery time	} $-di_F/dt = 100\text{ A}/\mu\text{s}$		$T_{VJ} = 25^\circ\text{C}$		150	ns
				$T_{VJ} = 100^\circ\text{C}$		300	ns



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0,4		0,6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI12-12A	DSEI12-12A	Tube	50	459801

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 150^{\circ}C$

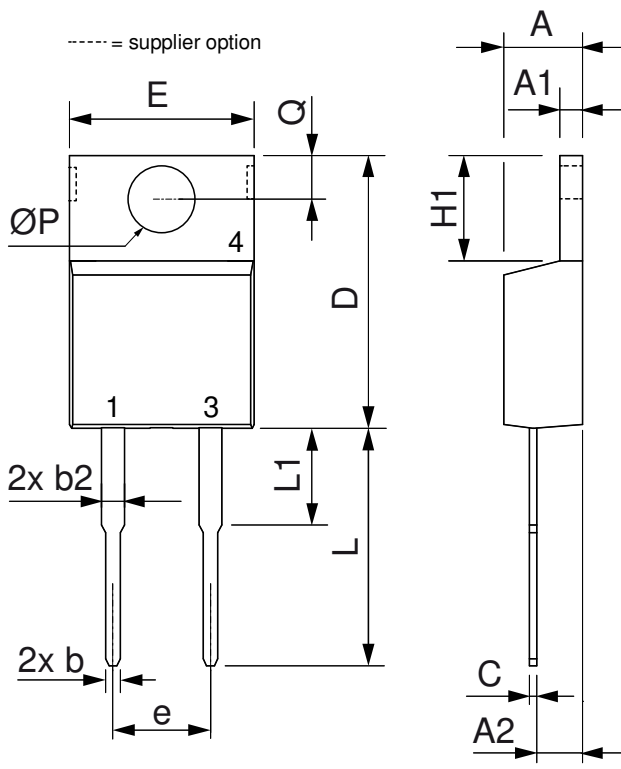


Fast Diode

$V_{0\ max}$	threshold voltage	1,77	V
$R_{0\ max}$	slope resistance *	35	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



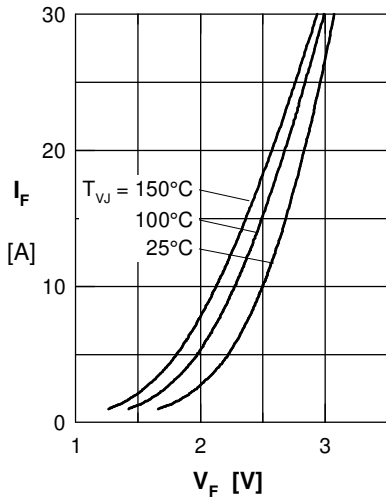
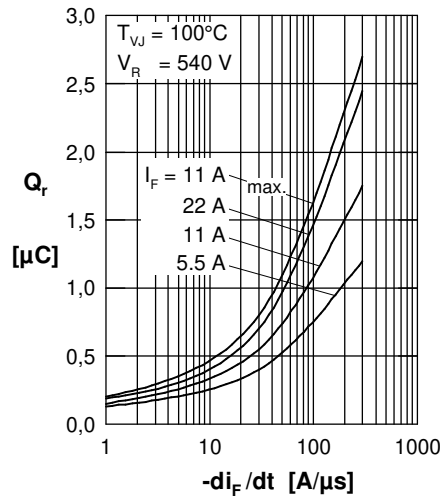
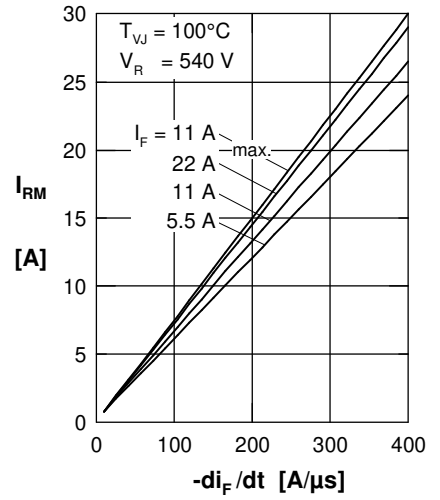
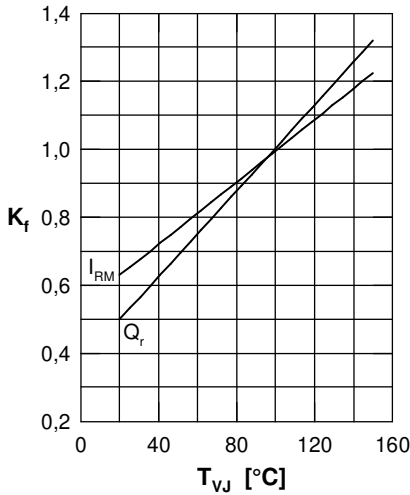
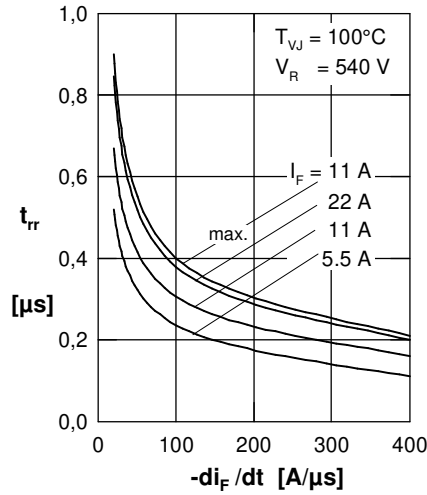
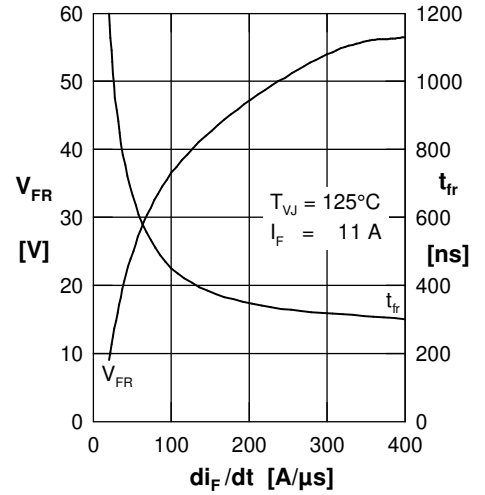
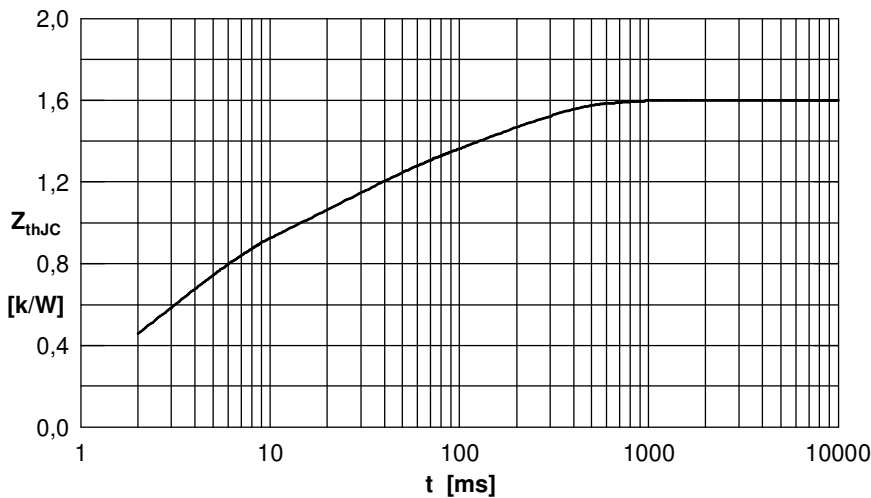
Fast Diode

 Fig. 1 Forward current I_F versus max. forward voltage drop V_F

 Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

 Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{tr} versus $-di_F/dt$

 Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt


Fig. 7 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.200	0.0018
2	0.220	0.0100
3	0.080	0.5000
4	0.300	0.0900
5	0.680	0.0300